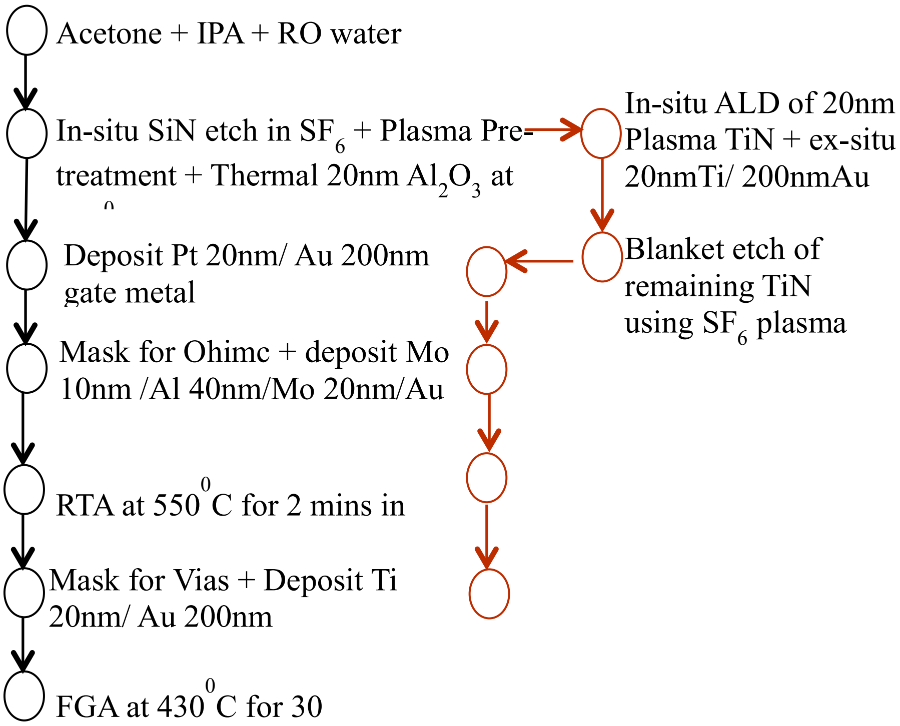

Fig 1: Process Flow

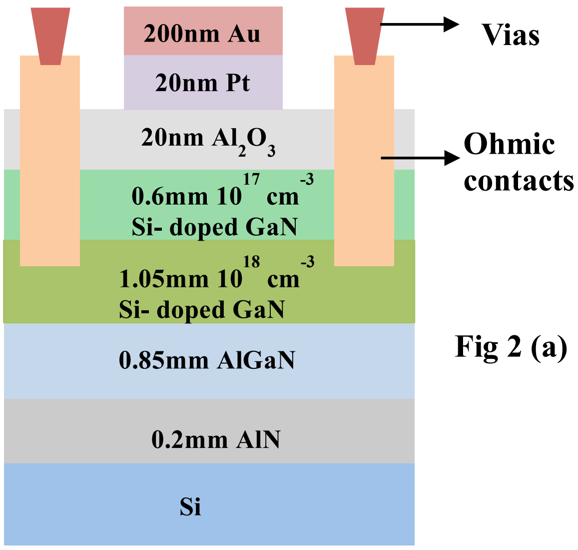

Fig 2 (a)

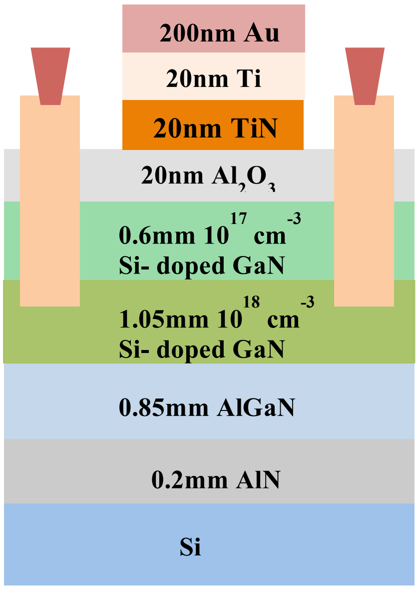

Fig 2 (b)

Figure 2(a) MOSCAP structure with Pt/Au and (b) with 20nm TiN + 20nm Ti/200nmAu

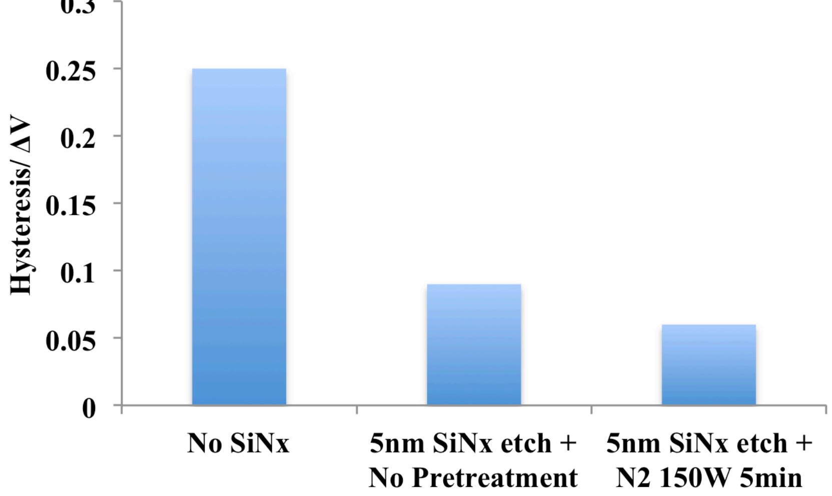

Fig 3: C-V Hysteresis with different processing

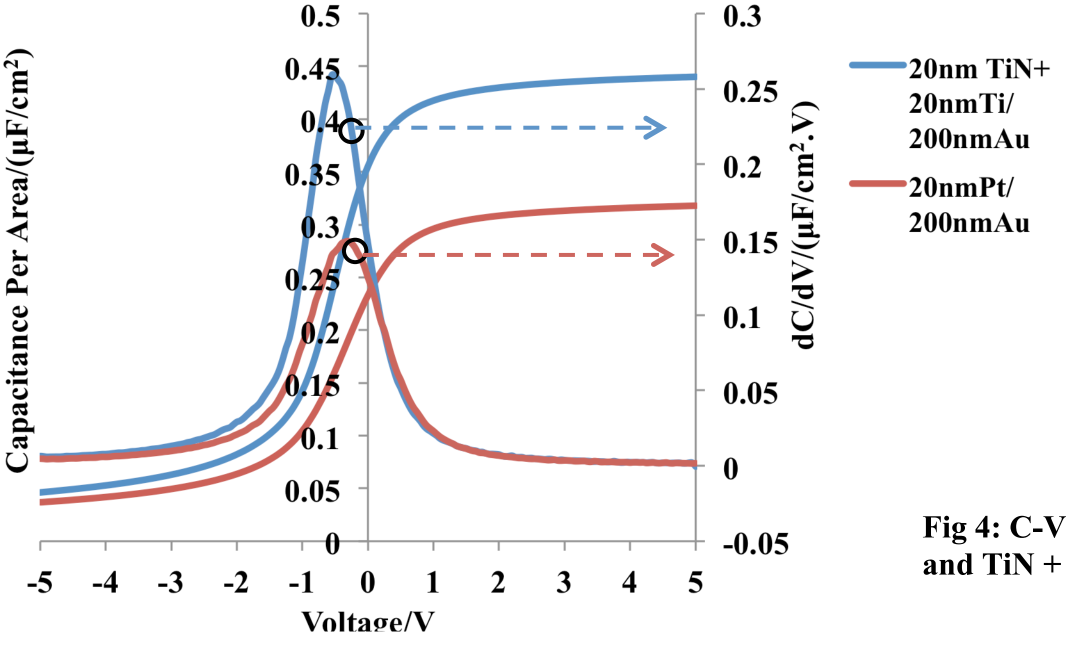

Fig 4: C-V and dC/dV data with Pt/Au and TiN + Ti/Au gate metal